

Website update – ESR-ER presentation template

Marie-Curie Fellow

Name: Vasiliauskas

First Name: Remigijus

Age: 26

Nationality: Lithuanian

Position (ER/ESR): ESR

Host institution: Linköping University

Contract duration: 3 years



Short Education Background (10 lines max.)

2007 – present - Linköping university, The Department of Physics, Chemistry and Biology, PhD studies in Material Science (Growth and Characterization of 3C-SiC).

2005 – 2007 - Vilnius University, Faculty of Physics, Master's degree in Material Science and Semiconductors Physics.

2001 – 2005 - Vilnius University, Faculty of Physics, Bachelor degree in Applied Physics.

Research focus and main activities carried out in the scope of the project (10 lines max.)

The work of the ESR Remigijus Vasiliauskas includes growth of 3C-SiC on hexagonal and cubic SiC substrates by Sublimation Epitaxy and characterization of the grown material by means of Optical Microscopy, Atomic Force Microscopy, X-Ray Diffraction and electrical measurements (C-V and Deep Level Transient Spectroscopy).

Since defects in the SiC need to be decreased the study will be focused on their qualitative and quantitative investigation and minimization of them by improving the growth.

Publications (please specify when the publication has been issued in the scope of the MANSiC project)

Journal papers

1. G. R. Yazdi, M. Syväjärvi, R. Vasiliauskas and R. Yakimova “Fabrication of free standing AlN crystals by controlled microrod growth” *Journal of Crystal Growth* V. 310 (2008) 935–939.

2. K. Neimontas, R. Vasiliauskas, A. Mekys, J. Storasta and K. Jarašiūnas “Characterization of electronic properties of SiC crystals by optical and electrical means” *Lithuanian Journal of Physics*, Vol. **48**, No. 1, pp. 79-84 (2008).

Conference papers

1. G. R. Yazdi, M. Syväjärvi, R. Vasiliauskas and R. Yakimova “Employing discontinuous and continuous growth modes for preparation of AlN nanostructures on SiC substrates” *Materials Science Forum* Vols. 556-557 (2007) pp. 1031-1034.

During MANSiC (only 2):

2. R. Vasiliauskas, M. Syväjärvi, M. Beshkova and R. Yakimova “Two-dimensional nucleation of cubic and 6H silicon carbide” *Materials Science Forum* Vols. 615-617 (2009) pp 189-192.

3. M. Beshkova, M. Syväjärvi, R. Vasiliauskas, J. Birch and R. Yakimova “Properties of 3C-SiC Grown by Sublimation Epitaxy” *Materials Science Forum* Vols. 615-617 (2009) pp 181-184.